

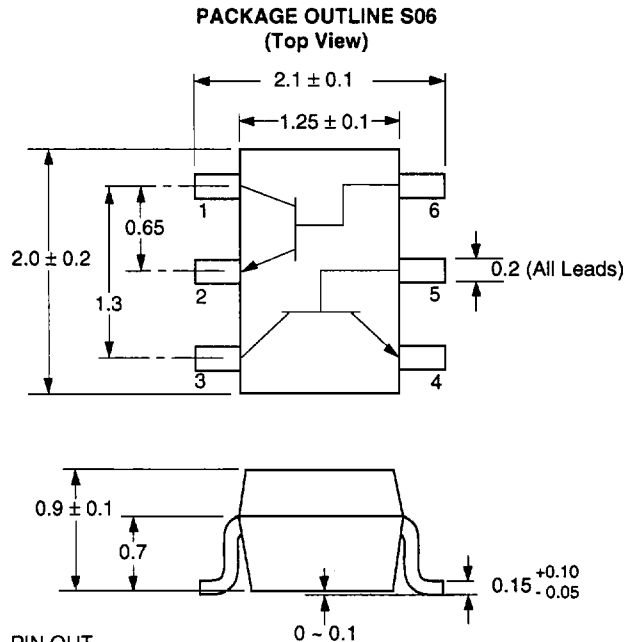
FEATURES

- **SMALL PACKAGE STYLE:**
2 NE681 Die in a 2 mm x 1.25 mm package
- **LOW NOISE FIGURE:**
NF = 1.4 dB TYP at 1 GHz
- **HIGH GAIN:**
 $|S_{21E}|^2 = 12$ dB TYP at 1 GHz
- **HIGH GAIN BANDWIDTH:** $f_T = 7$ GHz
- **LOW CURRENT OPERATION**

DESCRIPTION

The UPA802T is two NPN high frequency silicon epitaxial transistors encapsulated in an ultra small 6 pin SMT package. Each transistor is independently mounted and easily configured for either dual transistor or cascode operation. The high f_T , low voltage bias and small size make this device suited for various hand-held wireless applications.

OUTLINE DIMENSIONS (Units in mm)



- PIN OUT**
1. Collector Transistor 1
 2. Emitter Transistor 1
 3. Collector Transistor 2
 4. Emitter Transistor 2
 5. Base Transistor 2
 6. Base Transistor 1

Note:
Pin 3 is identified with a circle on the bottom of the package.



ELECTRICAL CHARACTERISTICS (T_A = 25°C)

PART NUMBER PACKAGE OUTLINE			UPA802T S06		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
I _{CBO}	Collector Cutoff Current at V _{CB} = 10 V, I _E = 0	μA			0.8
I _{EBO}	Emitter Cutoff Current at V _{EB} = 1 V, I _C = 0	μA			0.8
h _{FE1}	Forward Current Gain at V _{CE} = 3 V, I _C = 7 mA		70	100	240
f _r	Gain Bandwidth at V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	GHz	4.5	7.0	
C _{re} ²	Feedback Capacitance at V _{CB} = 3 V, I _E = 0, f = 1 MHz	pF			0.9
S _{21E} ²	Insertion Power Gain at V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	dB	10	12	
NF	Noise Figure at V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	dB		1.4	1.7
h _{FE1} /h _{FE2}	h _{FE} Ratio: h _{FE1} = Smaller Value of Q ₁ , or Q ₂ h _{FE2} = Larger Value of Q ₁ or Q ₂		0.85		

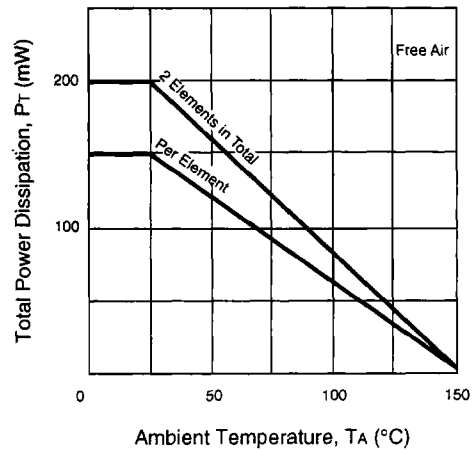
Notes: 1. Pulsed measurement, pulse width ≤ 350 μs, duty cycle ≤ 2%.
2. The emitter terminal should be connected to the ground terminal of the 3 terminal capacitance bridge.
For Tape and Reel version use part number UPA802T-T1, 3K per reel.

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CB0}	Collector to Base Voltage	V	20
V _{CE0}	Collector to Emitter Voltage	V	10
V _{EB0}	Emitter to Base Voltage	V	1.5
I _C	Collector Current	mA	65
PT	Total Power Dissipation	1 Die	mW 110
		2 Die	mW 200
T _J	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150

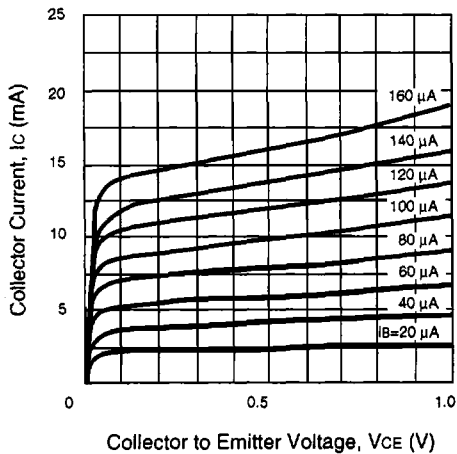
Note: 1. Operation in excess of any one of these parameters may result in permanent damage.

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

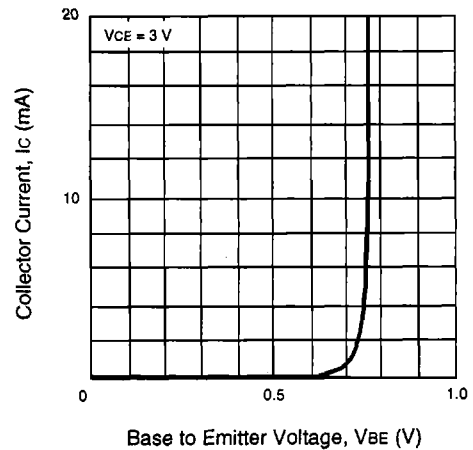


TYPICAL PERFORMANCE CURVES (T_A = 25°C)

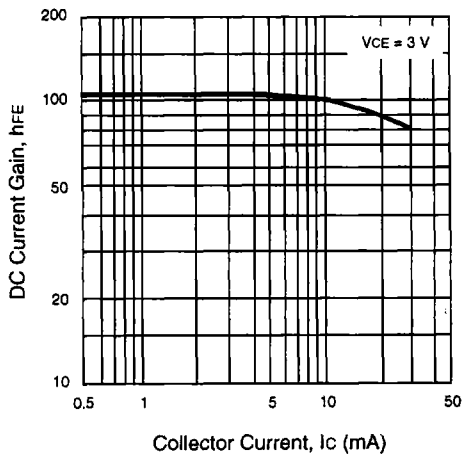
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



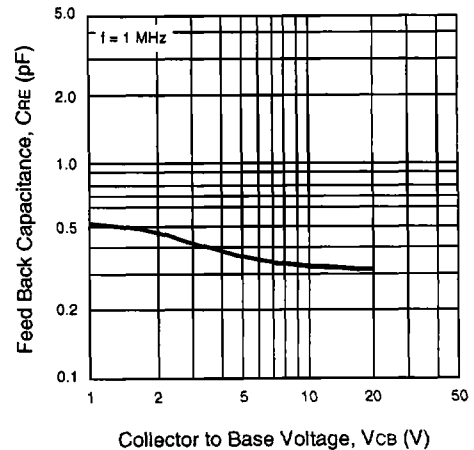
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



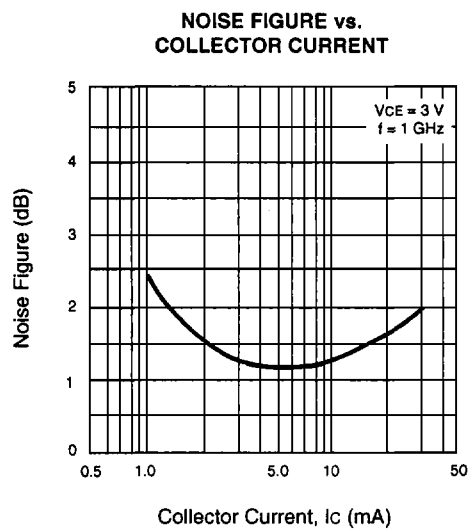
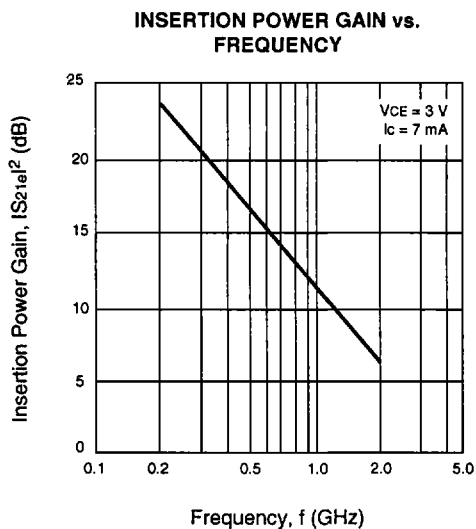
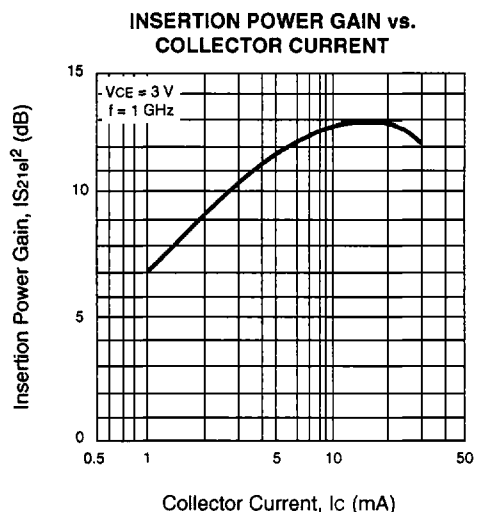
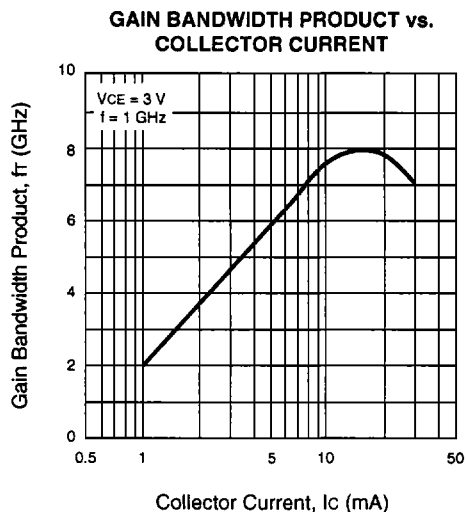
DC CURRENT GAIN vs. COLLECTOR CURRENT



FEED BACK CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)



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ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKAGING
UPA802T-T1	3000	Tape & Reel